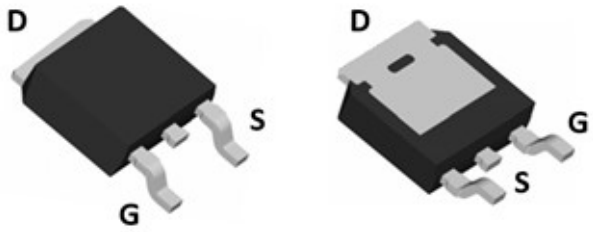
P-Channel Enhancement Mode Field Effect Transistor
RCD18P10

Product Summary

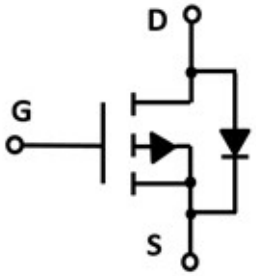
- V_{DS} -100V
- I_D -18A
- $R_{DS(ON)}$(at V_{GS}=-10V) ＜110 mohm
- $R_{DS(ON)}$(at V_{GS}=-4.5V) ＜120 mohm
- 100% UIS Tested
- 100% ▽V_{DS} Tested



General Description

- Split gate trench MOSFET technology
- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity

TO-252



Applications

- Power management
- Portable equipment

■ Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	-100	V
Gate-source Voltage		V_{GS}	±20	V
Drain Current	Tc=25℃	I_D	-18	A
	Tc=100℃		-12	
Pulsed Drain Current [A]		I_{DM}	-72	A
Avalanche energy [B]		E_{AS}	100	mJ
Total Power Dissipation	Tc=25℃	P_D	72	W
	Tc=100℃		28.8	
Junction and Storage Temperature Range		T_J ,T_{STG}	-55～+150	℃

■Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient [D]	t≤10S	$R_{\theta JA}$	15	20	℃/W
Thermal Resistance Junction-to-Ambient [D]	Steady-State		40	50	
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	1.35	1.7	

■ Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
RCD18P10	F1		2500	2500	250000	13“ reel

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■ Electrical Characteristics (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Conditions		Min	Typ	Max	Units
Static Parameter							
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=-250μA		-100			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-100V,V_{GS}=0V	T_j=25℃			-1	μA
			T_j=55℃			-5	
			T_j=125℃			-10	
Gate-Body Leakage Current	I_{GSS}	V_{GS}= ±20V, V_{DS}=0V				±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=-250μA		-1.0	-1.8	-2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}= -10V, I_D=-10A			83	110	mΩ
		V_{GS}= -4.5V, I_D=-5A			95	120	
Diode Forward Voltage	V_{SD}	I_S=-10A,V_{GS}=0V				-1.3	V
Maximum Body-Diode Continuous Current	I_S					-18	A
Dynamic Parameters							
Input Capacitance	C_{iss}	V_{DS}=-50V,V_{GS}=0V,f=1MHZ			1051		pF
Output Capacitance	C_{oss}				119		
Reverse Transfer Capacitance	C_{rss}				25		
Switching Parameters							
Total Gate Charge	$Q_{g(-10V)}$	V_{GS}=-10V,V_{DS}=-50V,I_D=-5A			20.1		nC
Total Gate Charge	$Q_{g(-4.5V)}$				9.7		
Gate-Source Charge	Q_{gs}				3.9		
Gate-Drain Charge	Q_{gd}				4.3		
Reverse Recovery Chrage	Q_{rr}	I_F=-5A, di/dt=100A/us			140		
Reverse Recovery Time	t_{rr}				70		ns
Turn-on Delay Time	$t_{D(on)}$	V_{GS}=-10V,V_{DD}=-50V,R_L=2.5Ω R_{GEN}=6Ω			10		
Turn-on Rise Time	t_r				30		
Turn-off Delay Time	$t_{D(off)}$				77		
Turn-off fall Time	t_f				81		

A. Repetitive rating; pulse width limited by max. junction temperature.
B. V_{DD}=50V, R_G=25Ω, L=0.5mH.
C. Pd is based on max. junction temperature, using junction-case thermal resistance.
D. The value of RθJA is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with TA =25° C. The Power dissipation PDSM is based on RθJA t≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

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■ Typical Performance Characteristics

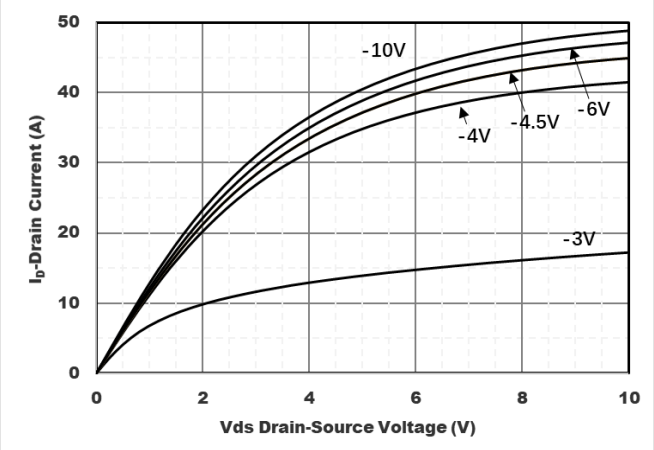

Figure1. Output Characteristics

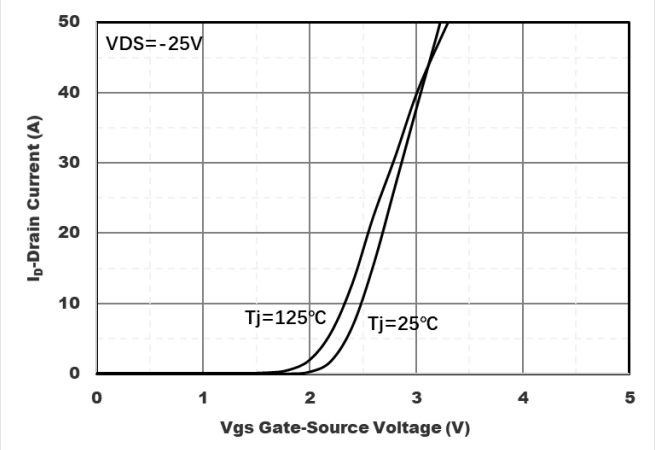

Figure2. Transfer Characteristics

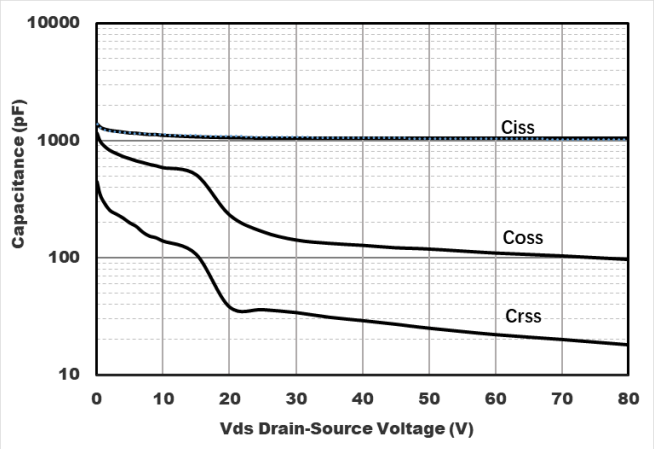

Figure3. Capacitance Characteristics

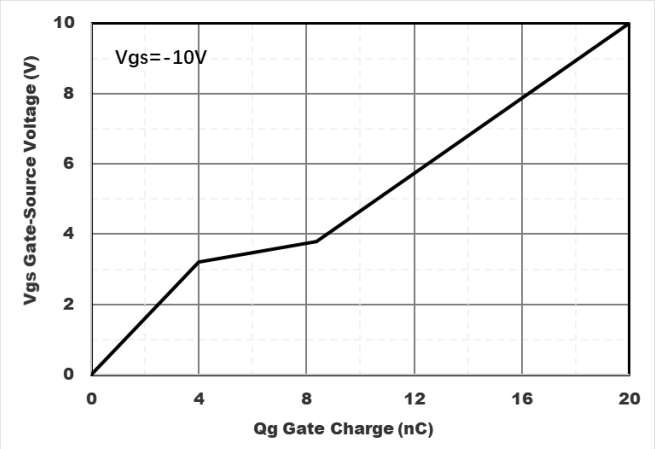

Figure4. Gate Charge

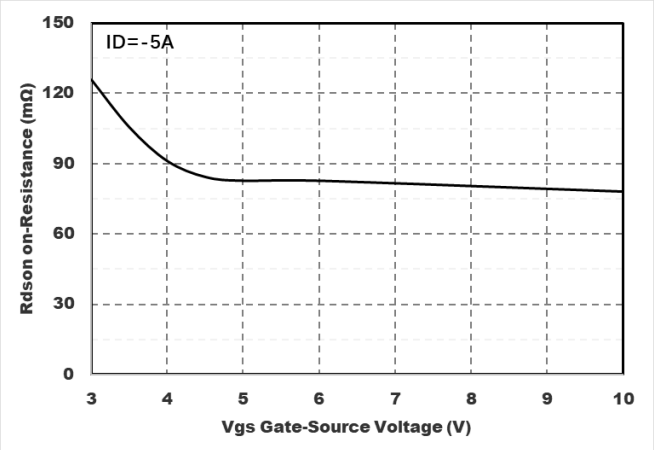

Figure5. : On-Resistance vs. Gate to Source Voltage

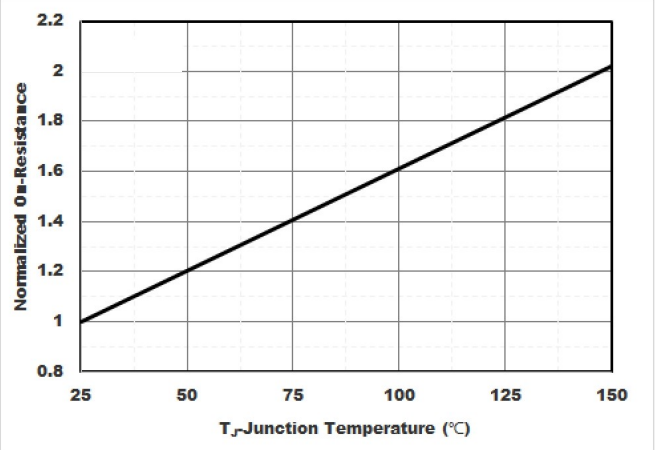

Figure6.Normalized On-Resistance

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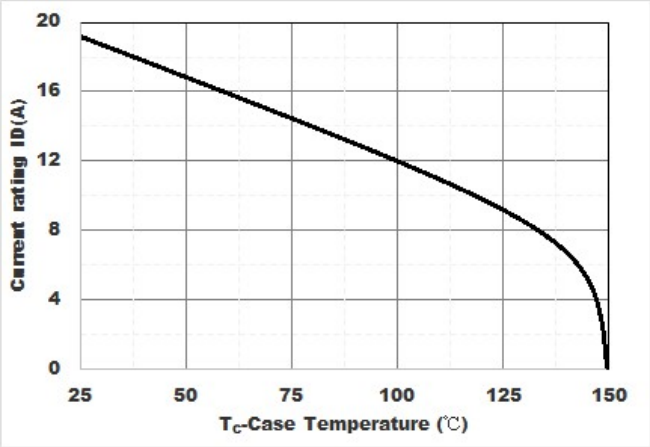

Figure7. Drain current

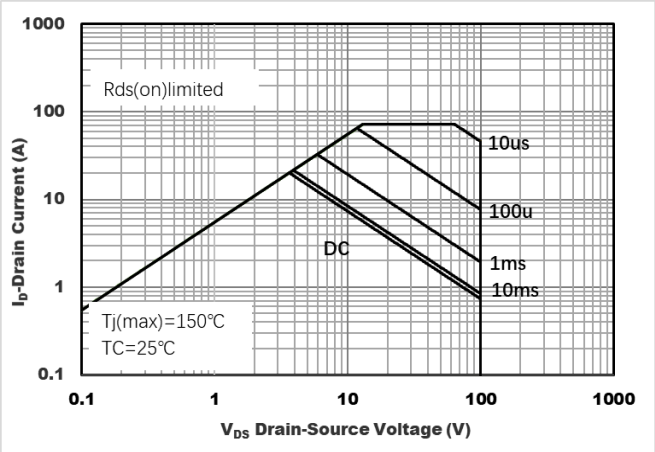

Figure8.Safe Operation Area

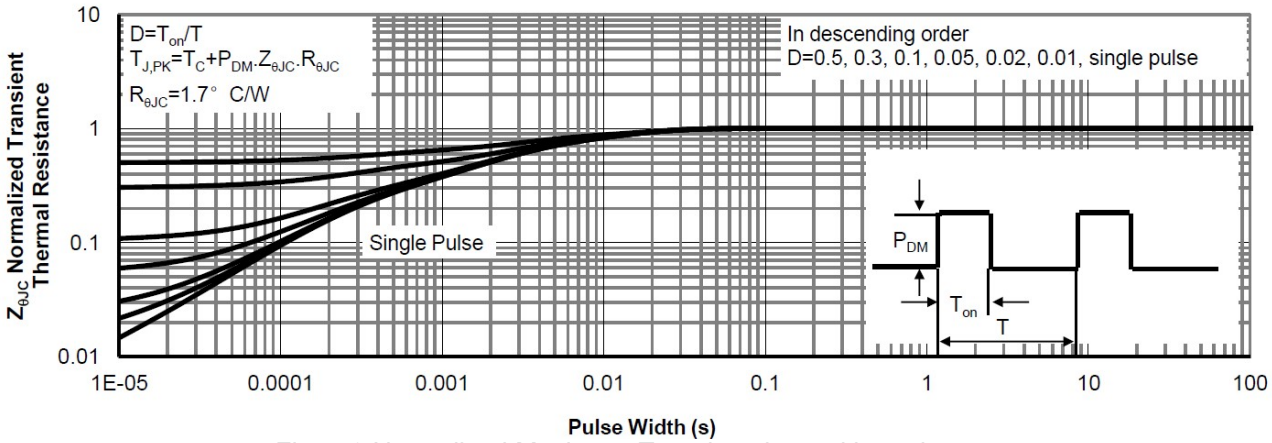

Figure9.Normalized Maximum Transient thermal impedance

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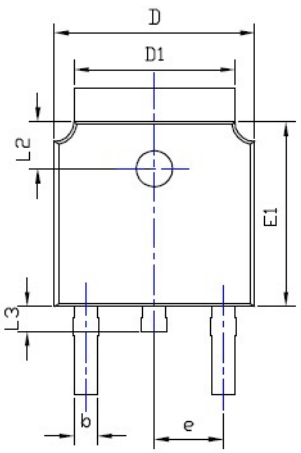
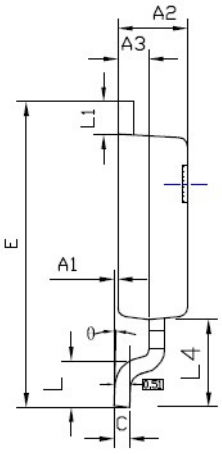
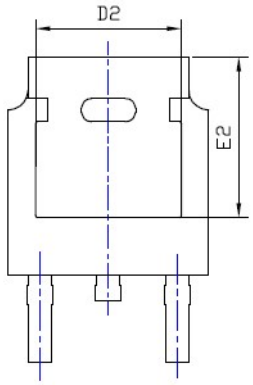
■ TO-252 Package information



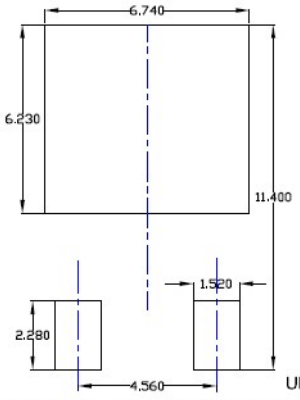
TOP VIEW



SIDE VIEW



BOTTOM VIEW



SUGGESTED SOLDER PAD LAYOUT

UNIT: mm

SYMBOL	DIMENSIONS					
	INCHES			Millimeter		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A1	0.000	---	0.008	0.000	---	0.200
A2	0.087	0.091	0.094	2.200	2.300	2.400
A3	0.035	0.039	0.043	0.900	1.000	1.100
b	0.026	0.030	0.034	0.660	0.760	0.860
c	0.018	0.020	0.023	0.460	0.520	0.580
D	0.256	0.260	0.264	6.500	6.600	6.700
D1	0.203	0.209	0.215	5.150	5.300	5.450
D2	0.181	0.189	0.195	4.600	4.800	4.950
E	0.390	0.398	0.406	9.900	10.100	10.300
E1	0.236	0.240	0.244	6.000	6.100	6.200
E2	0.203	0.209	0.215	5.150	5.300	5.450
e	0.090BSC			2.286BSC		
L	0.049	0.059	0.069	1.250	1.500	1.750
L1	0.035	---	0.050	0.900	---	1.270
L2	0.055	---	0.075	1.400	---	1.900
L3	0.240	0.310	0.039	0.600	0.800	1.000
L4	0.114REF			2.900REF		
θ	0°	---	10°	0°	---	10°